DATA SHEET



BIPOLAR ANALOG INTEGRATED CIRCUIT

μ PC8179TK

3 V SILICON MMIC LOW CURRENT AMPLIFIER FOR MOBILE COMMUNICATIONS

DESCRIPTION

The μ PC8179TK is a silicon monolithic integrated circuit designed as amplifier for mobile communications. This IC can realize low current consumption with external chip inductor which can not be realized on internal 50 Ω wide band matched IC. μ PC8179TK adopts 6-pin lead-less minimold package using same chip as the conventional μ PC8179TB in 6-pin super minimold.

TK suffix IC which is smaller package than TB suffix IC contributes to reduce mounting space by 50%.

This IC is manufactured using our 30 GHz fmax UHS0 (Ultra High Speed Process) silicon bipolar process.

FEATURES

Low current consumption : Icc = 4.0 mA TYP. @ Vcc = 3.0 V

Supply voltage : Vcc = 2.4 to 3.3 V

• Excellent isolation : ISL = 43.0 dB TYP. @ f = 1.0 GHz

ISL = 42.0 dB TYP. @ f = 1.9 GHzISL = 42.0 dB TYP. @ f = 2.4 GHz

Power gain : G_P = 13.5 dB TYP. @ f = 1.0 GHz

 $G_P = 15.5 \text{ dB TYP.}$ @ f = 1.9 GHz $G_P = 16.0 \text{ dB TYP.}$ @ f = 2.4 GHz

• Gain 1 dB compression output power: Po (1 dB) = +2.0 dBm TYP. @ f = 1.0 GHz

Po (1 dB) = +0.5 dBm TYP. @ f = 1.9 GHz Po (1 dB) = +0.5 dBm TYP. @ f = 2.4 GHz

Operating frequency : 0.1 to 2.4 GHz (Output port LC matching)

• High-density surface mounting : 6-pin lead-less minimold package (1.5 \times 1.3 \times 0.55 mm)

Light weight : 3 mg (Standard value)

APPLICATION

· Buffer amplifiers on 0.1 to 2.4 GHz mobile communications system

Caution: Observe precautions when handling because these devices are sensitive to electrostatic discharge

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

ORDERING INFORMATION

Part Number	Order Number	Package	Marking	Supplying Form
μPC8179TK-E2	μPC8179TK-E2-A	6-pin lead-less minimold (1511) (Pb-Free) Note	6C	Embossed tape 8 mm wide Pin 1, 6 face the perforation side of the tape Qty 5 kpcs/reel

Note With regards to terminal solder (the solder contains lead) plated products (conventionally plated), contact your nearby sales office.

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: μ PC8179TK-A

PRODUCT LINE-UP (TA = +25°C, Vcc = Vout = 3.0 V, Zs = ZL = 50 Ω)

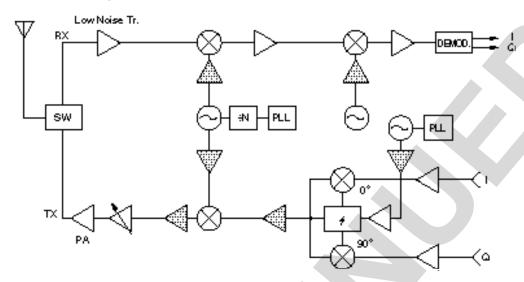
Parameter 1.0 GHz output matching frequ		•	1.66 GHz output port matching frequency		1.9 GHz output port matching frequency		2.4 GHz output port matching frequency			Marking				
Part No.	Icc (mA)	G _P (dB)	ISL (dB)	Po (1dB) (dBm)	G _P (dB)	ISL (dB)	Po (1dB) (dBm)	G _P (dB)	ISL (dB)	Po (1dB) (dBm)	G _P (dB)	ISL (dB)	Po (1dB) (dBm)	
μPC8178TB	1.9	11.0	39.0	-4.0	-	-	=	11.5	40.0	-7.0	11.5	38.0	-7.5	СЗВ
μPC8178TK	1.9	11.0	40.0	-5.5	-	-4	-	11.0	41.0	-8.0	11.0	42.0	-8.0	6B
μPC8179TB	4.0	13.5	44.0	+3.0	-	-	-	15.5	42.0	+1.5	15.5	41.0	+1.0	C3C
μPC8179TK	4.0	13.5	43.0	+2.0	-	-	=	15.5	42.0	+0.5	16.0	42.0	+0.5	6C
μPC8128TB	2.8	12.5	39.0	-4.0	13.0	39.0	-4.0	13.0	37.0	-4.0	-	-	-	C2P
μPC8151TB	4.2	12.5	38.0	+2.5	15.0	36.0	+1.5	15.0	34.0	+0.5	П	=	=	C2U
μPC8152TB	5.6	23.0	40.0	-4.5	19.5	38.0	-8.5	17.5	35.0	-8.5	I	=	_	C2V

Remarks 1. Typical performance. Please refer to **ELECTRICAL CHARACTERISTICS** in detail.

2. To know the associated product, please refer to each latest data sheet.

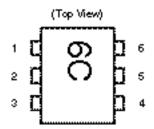
SYSTEM APPLICATION EXAMPLE

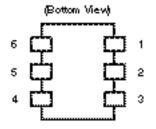
Location examples in digital cellular



These ICs can be added to your system around 🖺 parts, when you need more isolation or gain. The application herein, however, shows only examples, therefore the application can depend on your kit evaluation.

PIN CONNECTIONS





Pin No.	Pin Name
1	INPUT
2	GND
3	GND
4	OUTPUT
5	GND
6	Vcc

PIN EXPLANATION

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V)	Function and Applications	Internal Equivalent Circuit
1	INPUT	-	0.90	Signal input pin. A internal matching circuit, configured with resisters, enables $50~\Omega$ connection over a wide band. This pin must be coupled to signal source with capacitor for DC cut.	
2 3 5	GND	0	-	Ground pin. This pin should be connected to system ground with minimum inductance. Ground pattern on the board should be formed as wide as possible. All the ground pins must be connected together with wide ground pattern to decrease impedance defference.	
4	OUTPUT	Voltage as same as Vcc through external inductor		Signal output pin. This pin is designed as collector output. Due to the high impedance output, this pin should be externally equipped with LC matching circuit to next stage. For L, a size 1 005 chip inductor can be chosen.	
6	Vcc	2.4 to 3.3	-	Power supply pin. This pin should be externally equipped with bypass capacitor to minimize its impedance.	

Note Pin voltage is measured at Vcc = 3.0 V.

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Test Conditions	Ratings	Unit
Supply Voltage	Vcc	T _A = +25°C, Pin 4, Pin 6	3.6	V
Circuit Current	Icc	T _A = +25°C	15	mA
Power Dissipation	Po	T _A = +85°C Note	232	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	Tstg		-55 to +150	°C
Input Power	Pin	T _A = +25°C	+5	dBm

Note Mounted on double-sided copper-clad $50 \times 50 \times 1.6$ mm epoxy glass PWB

RECOMMENDED OPERATING RANGE

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Remarks
Supply Voltage	Vcc	2.4	3.0	3.3	V	The same voltage should be applied to pin 4 and pin 6.
Operating Ambient Temperature	TA	-40	+25	+85	°C	

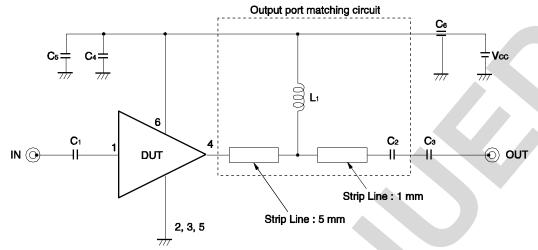
ELECTRICAL CHARACTERISTICS

(Unless otherwise specified, $T_A = +25^{\circ}C$, $V_{CC} = V_{out} = 3.0$ V, $Z_S = Z_L = 50$ Ω , at LC matched frequency)

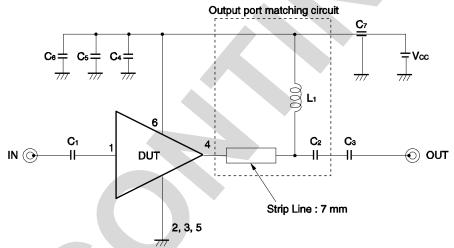
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Circuit Current	Icc	No signal	2.9	4.0	5.4	mA
Power Gain	GР	f = 1.0 GHz, P _{in} = -30 dBm	11.0	13.5	15.5	dB
		$f = 1.9 \text{ GHz}, P_{in} = -30 \text{ dBm}$	13.0	15.5	17.5	
		$f = 2.4 \text{ GHz}, P_{in} = -30 \text{ dBm}$	14.0	16.0	18.5	
Isolation	ISL	f = 1.0 GHz, Pin = -30 dBm	39.0	43.0	-	dB
		f = 1.9 GHz, Pin = -30 dBm	37.0	42.0	-	
		f = 2.4 GHz, Pin = -30 dBm	37.0	42.0	-	
Gain 1 dB Compression Output	Po (1 dB)	f = 1.0 GHz	-0.5	+2.0	-	dBm
Power		f = 1.9 GHz	-2.0	+0.5	=	
		f = 2.4 GHz	-3.0	+0.5	=	
Noise Figure	NF	f = 1.0 GHz	_	5.0	6.5	dB
		f = 1.9 GHz	=	5.0	6.5	
		f = 2.4 GHz	-	5.0	6.5	
Input Return Loss	RLin	f = 1.0 GHz, Pin = -30 dBm	4.0	7.0	-	dB
		f = 1.9 GHz, Pin = -30 dBm	4.0	7.0	-	
		f = 2.4 GHz, Pin = -30 dBm	6.0	9.0	-	

TEST CIRCUITS

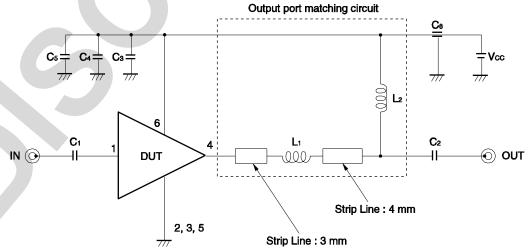
<1> f = 1.0 GHz



<2> f = 1.9 GHz

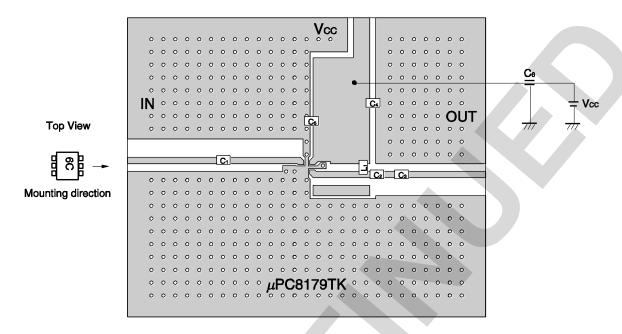


<3> f = 2.4 GHz



■ ILLUSTRATION OF THE TEST CIRCUIT ASSEMBLED ON EVALUATION BOARD

<1> f = 1.0 GHz



Remarks 1. $42 \times 35 \times 0.4$ mm double-sided copper-clad polyimide board

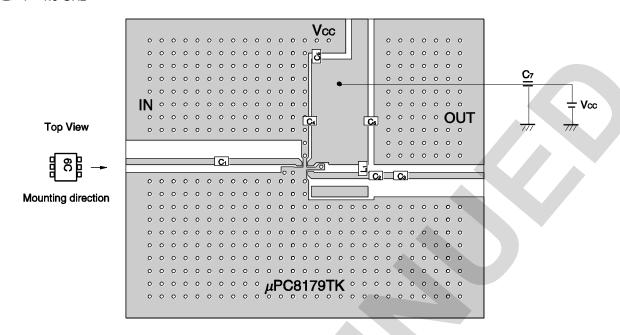
Back side: GND pattern
 Gold plated on pattern

4. o:Through holes

COMPONENT LIST

Form	Symbol	Value	Type code	Maker
Chip capacitor	C ₁ , C ₃	1 000 pF	GRM40CH102J50PT	murata
	C ₂	0.75 pF	GRM39CKR75C50PT	murata
	C ₄	5 pF	GRM39CH050C50PT	murata
	C ₅	8 pF	GRM39CH080D50PT	murata
Feed-though Capacitor	C ₆	1 000 pF	DFT301-801 × 7R102S50	murata
Chip inductor	L ₁	12 nH	LL1608-FH12N	токо

<2> f = 1.9 GHz



Remarks 1. $42 \times 35 \times 0.4$ mm double-sided copper-clad polyimide board

2. Back side: GND pattern

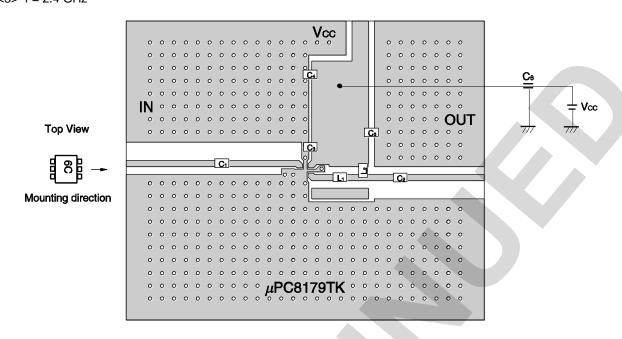
3. Gold plated on pattern

4. o:Through holes

COMPONENT LIST

Form	Symbol	Value	Type code	Maker
Chip capacitor	C1, C3, C5, C6	1 000 pF	GRM40CH102J50PT	murata
	C ₂	0.5 pF	GRM39CKR5C50PT	murata
	C ₄	8 pF	GRM39CH080D50PT	murata
Feed-though Capacitor	C 7	1 000 pF	DFT301-801 × 7R102S50	murata
Chip inductor	L ₁	2.7 nH	LL1608-FH2N7S	токо

<3> f = 2.4 GHz



Remarks 1. $42 \times 35 \times 0.4$ mm double-sided copper-clad polyimide board

2. Back side: GND pattern

3. Gold plated on pattern

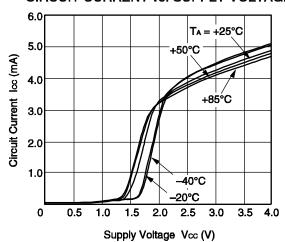
4. o:Through holes

COMPONENT LIST

Form	Symbol	Value	Type code	Maker
Chip capacitor	C1, C2, C4, C5	1 000 pF	GRM40CH102J50PT	murata
	C ₃	10 pF	GRM39CH100D50PT	murata
Feed-though Capacitor	C ₆	1 000 pF	DFT301-801 × 7R102S50	murata
Chip inductor	Li	2.7 nH	LL1608-FH2N7S	токо
	L ₂	1.8 nH	LL1608-FH1N8S	токо

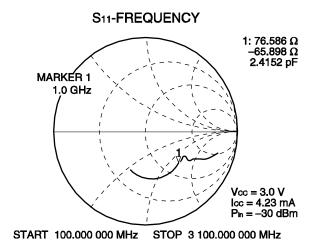
★ TYPICAL CHARACTERISTICS (T_A = +25°C, unless otherwise specified)

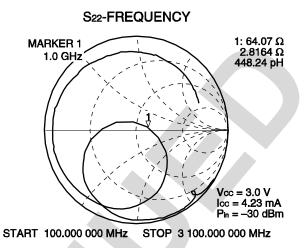
CIRCUIT CURRENT vs. SUPPLY VOLTAGE

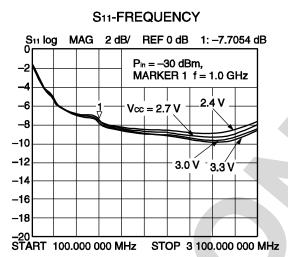


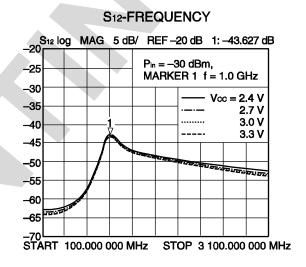
Remark The graph indicates nominal characteristics.

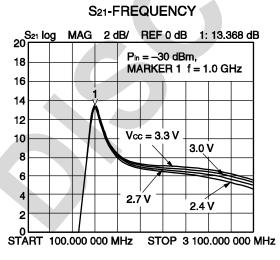
f = 1.0 GHz MATCHING

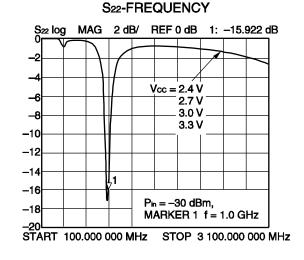






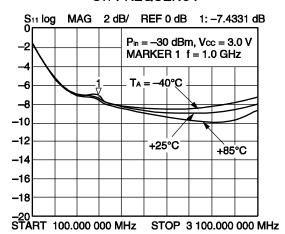




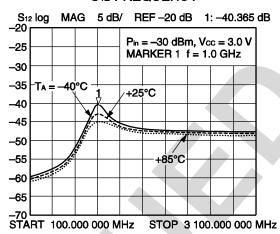


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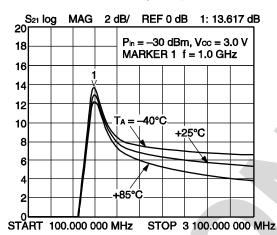
S₁₁-FREQUENCY



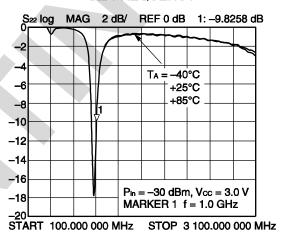
S₁₂-FREQUENCY



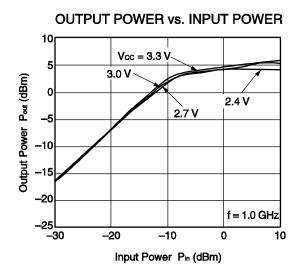
S21-FREQUENCY

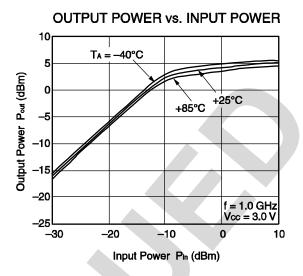


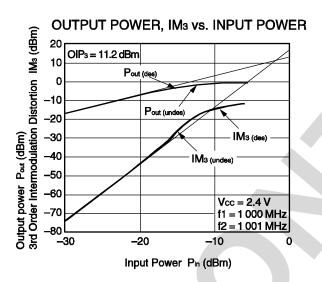
S22-FREQUENCY

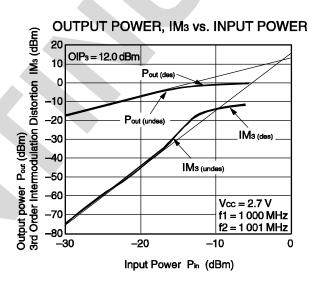


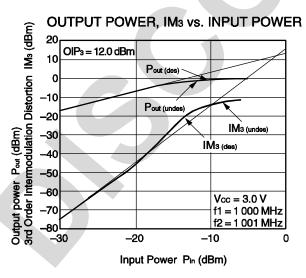
Remark The graphs indicate nominal characteristics.

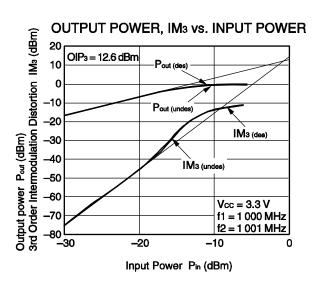




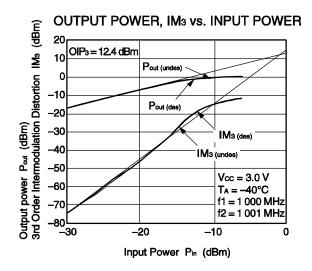


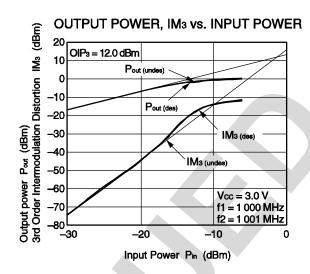


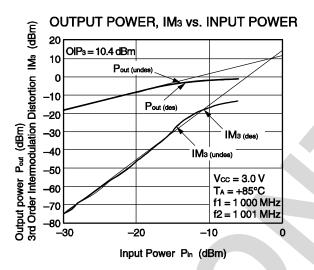


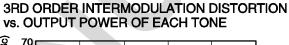


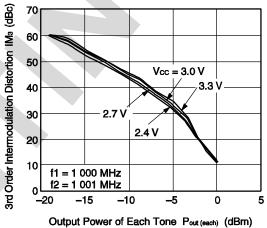
Remark The graphs indicate nominal characteristics.

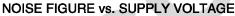


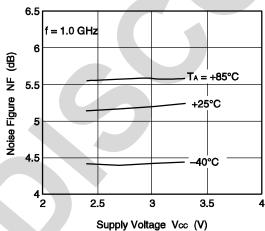






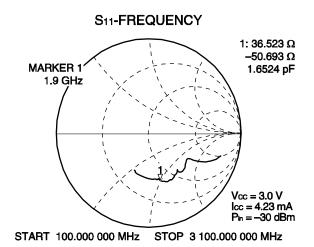


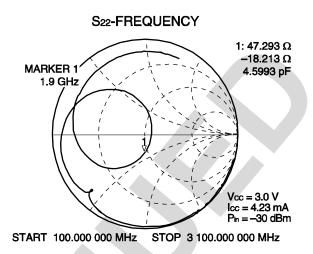


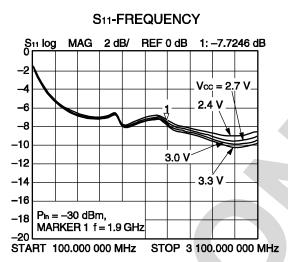


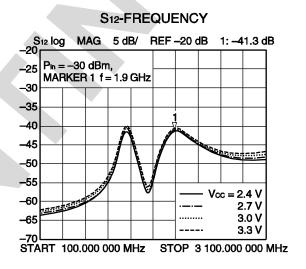
Remark The graphs indicate nominal characteristics.

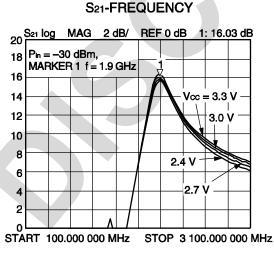
f = 1.9 GHz MATCHING

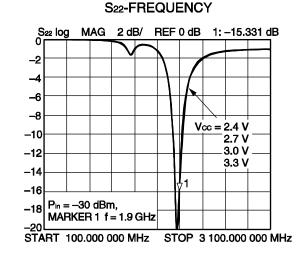






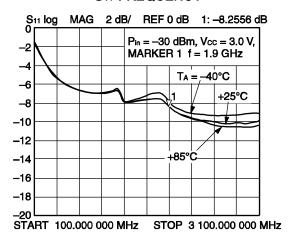




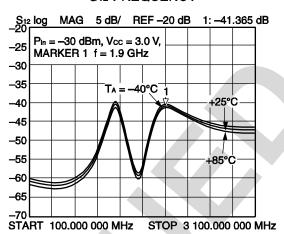


Remark The graphs indicate nominal characteristics.

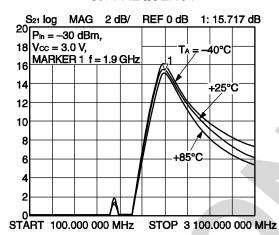
S₁₁-FREQUENCY



S₁₂-FREQUENCY

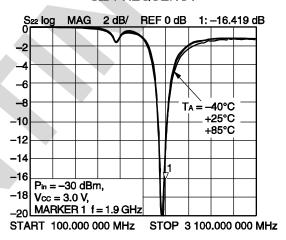


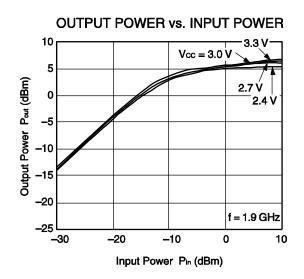
S21-FREQUENCY

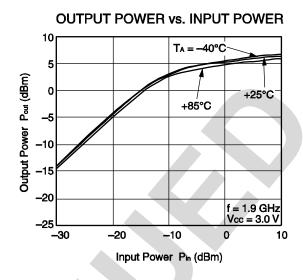


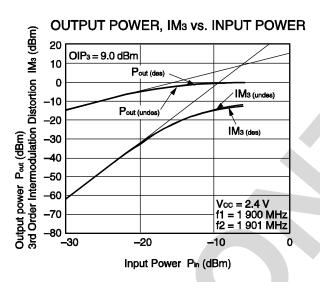
Remark The graphs indicate nominal characteristics.

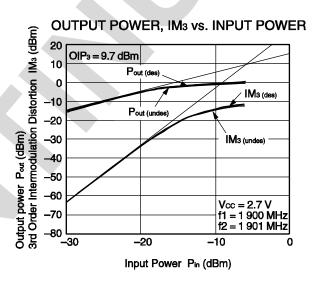
S22-FREQUENCY

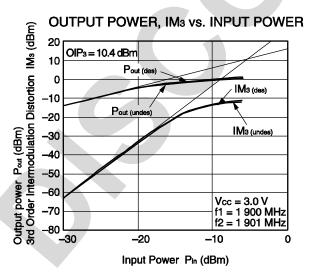


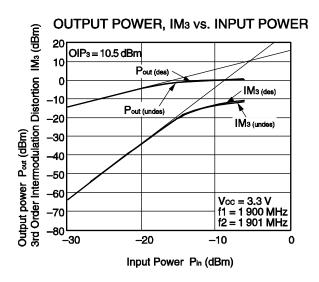




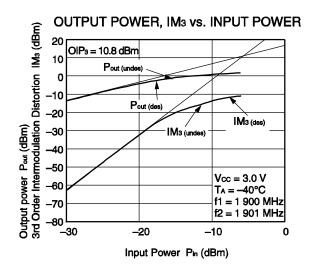


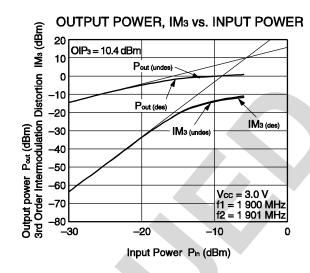


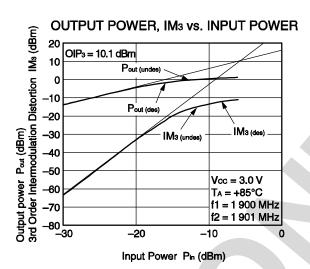


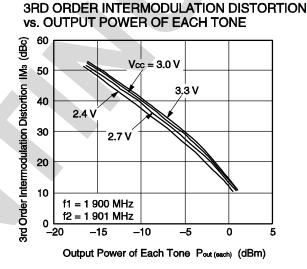


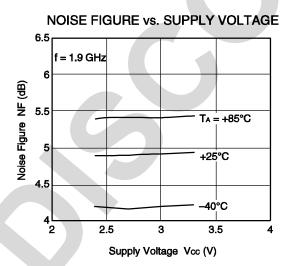
Remark The graphs indicate nominal characteristics.





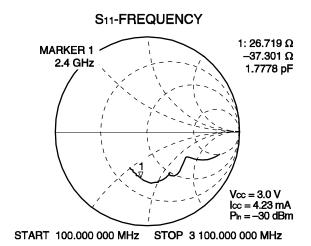


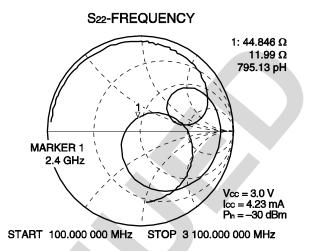


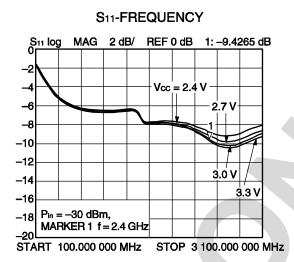


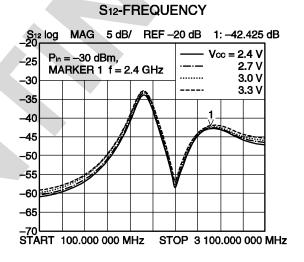
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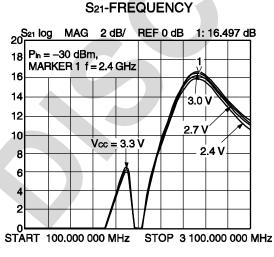
f = 2.4 GHz MATCHING

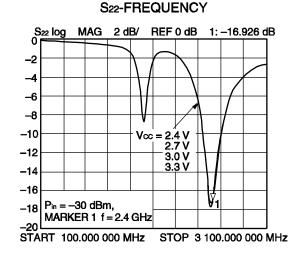






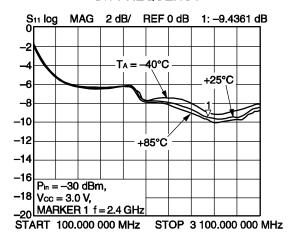




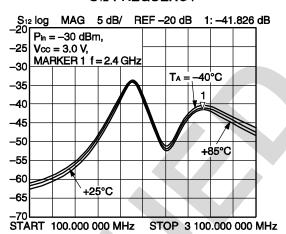


Remark The graphs indicate nominal characteristics.

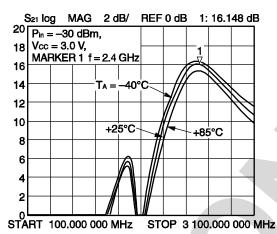
S₁₁-FREQUENCY



S₁₂-FREQUENCY

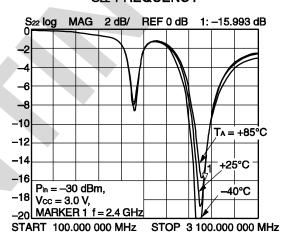


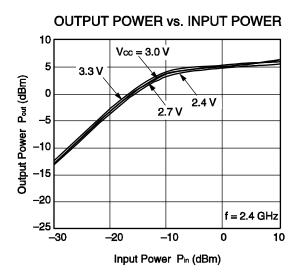
S21-FREQUENCY

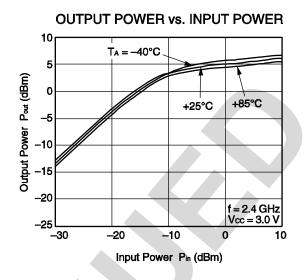


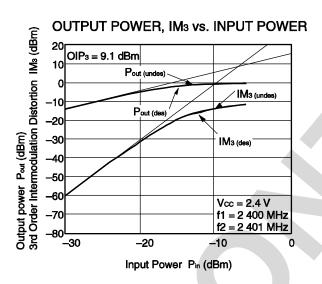
Remark The graphs indicate nominal characteristics.

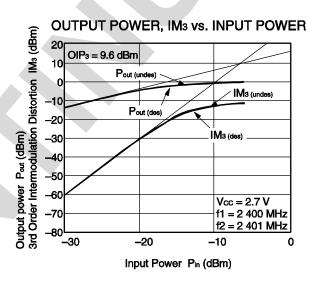
S22-FREQUENCY

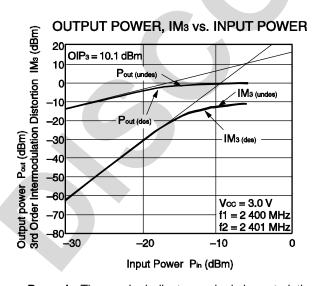


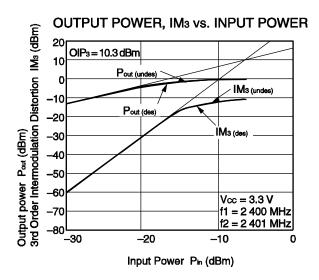




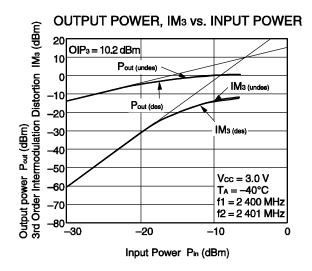


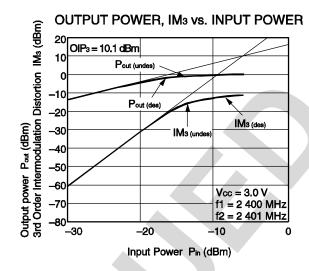


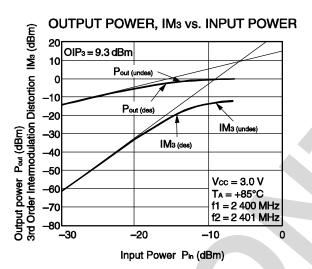


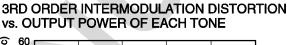


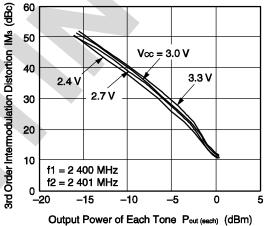
Remark The graphs indicate nominal characteristics.

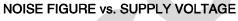


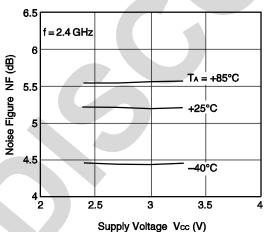












Remark The graphs indicate nominal characteristics.

f = 3.0 GHz MATCHING

S₁₁-FREQUENCY 1:•77.02 Ω -65.883 Ω -MARKER 4 • 1 GHz 3 GHz 2:•37.43 Ω -53.027 Ω • 1.9 GHz / 3:•28.781 Ω -39.209 Ω 2.4 GHz/ 4:•25.676 Ω –27.78 Ω • 1.9097 pF Vcc = 3.0 Vlcc = 4.23 mAPin = -30 dBm $T_A = +25^{\circ}C$ (at L loaded) STOP 3 100.000 000 MHz START 100.000 000 MHz

Remark The graphs indicate nominal characteristics.

S22-FREQUENCY 1:•96.859 Ω -359.69 Ω • 1 GHz 2:•54.43 Ω -218.02 Ω • 1.9 GHz 3:•41.422 Ω -181.84 Ω • 2.4 GHz 4:•27.039 Ω -151.69 Ω • 349.74 fF Vcc = 3.0 V Icc = 4.23 mA Pn = -30 dBm TA = +25°C (at L loaded)

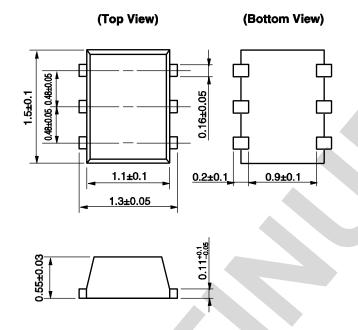
STOP 3 100.000 000 MHz

START 100.000 000 MHz

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PACKAGE DIMENSIONS

6-PIN LEAD-LESS MINIMOLD (1511) (UNIT: mm)



NOTE ON CORRECT USE

- (1) Observe precautions for handling because of electro-static sensitive devices.
- (2) Form a ground pattern as widely as possible to minimize ground impedance (to prevent undesired oscillation). All the ground pins must be connected together with wide ground pattern to decrease impedance difference.
- (3) The bypass capacitor should be attached to Vcc line.
- (4) The inductor (L) should be attached between output and Vcc pins. The L and series capacitor (C) values should be adjusted for applied frequency to match impedance to next stage.
- (5) The DC capacitor must be attached to input pin.

RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature)	: 260°C or below	IR260
	Time at peak temperature	: 10 seconds or less	
	Time at temperature of 220°C or higher	: 60 seconds or less	
	Preheating time at 120 to 180°C	: 120±30 seconds	
	Maximum number of reflow processes	: 3 times	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	
Wave Soldering	Peak temperature (molten solder temperature)	: 260°C or below	WS260
	Time at peak temperature	: 10 seconds or less	
	Preheating temperature (package surface temperature)	: 120°C or below	
	Maximum number of flow processes	: 1 time	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	
Partial Heating	Peak temperature (terminal temperature)	: 350°C or below	HS350
	Soldering time (per side of device)	: 3 seconds or less	
	Maximum chlorine content of rosin flux (% mass)	: 0.2%(Wt.) or below	

Caution Do not use different soldering methods together (except for partial heating).



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